Switching diode

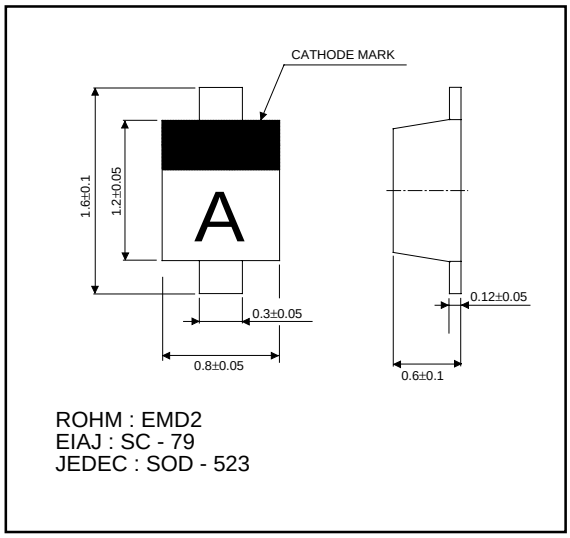
1SS400

●**Applications**
High speed switching

●**Features**
1) Extremely small surface mounting type.(EMD2)
2) High Speed.(t_{rr}=1.2ns Typ.)
3) High reliability.

●**Construction**
Silicon epitaxial planar

●**External dimensions** (Units : mm)



ROHM : EMD2
EIAJ : SC - 79
JEDEC : SOD - 523

●**Absolute maximum ratings** (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_O	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−55 ~ +125	°C

●**Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	1.2	V	I_F=100mA
Reverse current	I_R	–	–	0.1	μA	V_R=80V
Capacitance between terminals	C_T	–	0.72	3.0	pF	V_R=0.5V , f=1MHz
Reverse recovery time	t_{rr}	–	–	4	ns	V_R=6V , I_F=10mA , R_L=100Ω

●**Electrical characteristic curves** (Ta = 25°C)

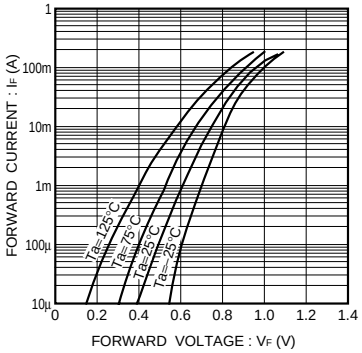


Fig.1 Forward characteristics

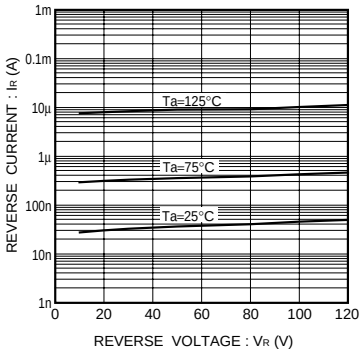


Fig.2 Reverse characteristics

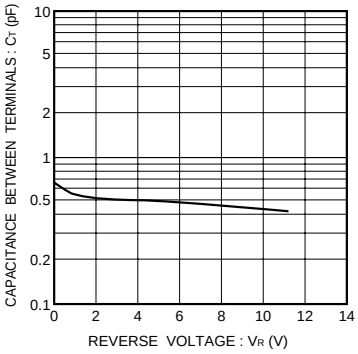


Fig.3 Capacitance between terminals

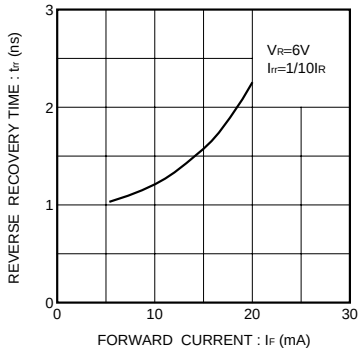


Fig.4 Reverse recovery time characteristics

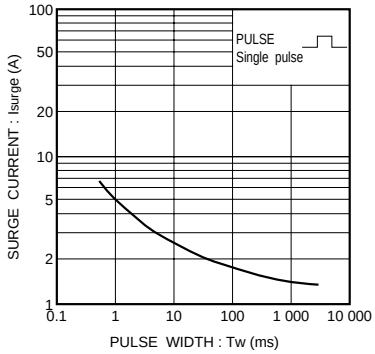


Fig.5 Surge current characteristics

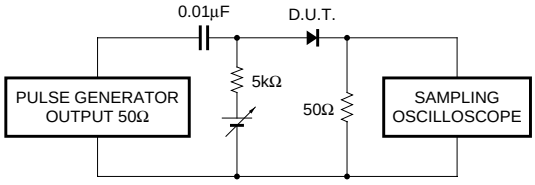


Fig.6 Reverse recovery time (t_{rr}) measurement circuit